

RT2A00M

COMPOSITE TRANSISTOR
FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

RT2A00M is a composite transistor built with two 2SA1602A chips in SC-88 package.

FEATURE

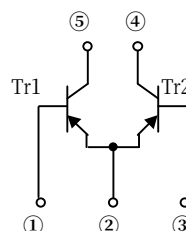
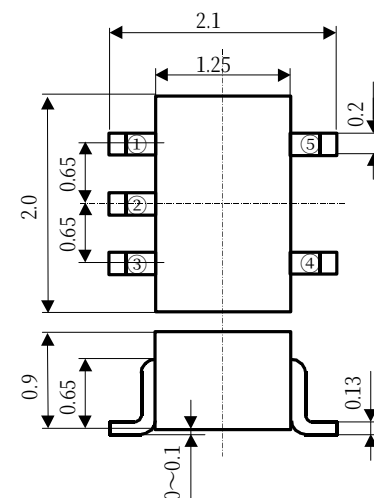
- Silicon pnp epitaxial type
Each transistor elements are independent.
- Mini package for easy mounting

APPLICATION

For low frequency amplify application

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ①: BASE1
- ②: EMITTER (COMMON)
- ③: BASE2
- ④: COLLECTOR2
- ⑤: COLLECTOR1

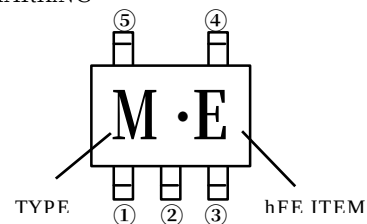
JEITA: —

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MAXIMUM RATINGS (Ta=25°C (Tr1, Tr2)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	-60	V
V_{EBO}	Emitter to Base voltage	-6	V
V_{CEO}	Collector to Emitter voltage	-50	V
I_C	Collector current	-200	mA
P_C	Collector dissipation (Total Ta=25°C)	150	mW
T_j	Junction temperature	+125	°C
T_{stg}	Storage temperature	-55~+125	°C

MARKING



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ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1, Tr2)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	Collector to Emitter break down voltage	$I_C = -100 \mu A$, $R_{BE} = \infty$	-50	-	-	V
I_{CBO}	Collector cut off current	$V_{CB} = -60V$, $I_E = 0mA$	-	-	-0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -6V$, $I_C = 0mA$	-	-	-0.1	μA
h_{FE}^*	DC forward current gain	$V_{CE} = -6V$, $I_C = -1mA$	150	-	800	-
h_{FE}	DC forward current gain	$V_{CE} = -6V$, $I_C = -0.1mA$	90	-	-	-
$V_{CE(sat)}$	Collector to Emitter saturation voltage	$I_C = -100mA$, $I_B = -10mA$	-	-	-0.3	V
f_T	Gain band width product	$V_{CE} = -6V$, $I_E = 10mA$	-	200	-	MHz
Cob	Collector output capacitance	$V_{CB} = -6V$, $I_E = 0mA$, $f = 1MHz$	-	4.0	-	pF
NF	Noise figure	$V_{CE} = -6V$, $I_E = 0.3mA$, $f = 100Hz$, $R_G = 10k\Omega$	-	-	20	dB

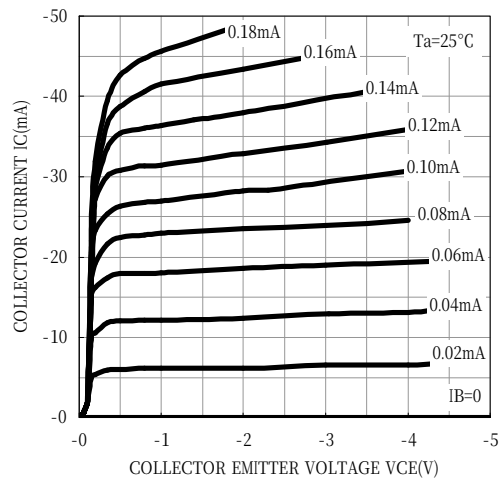
*: It shows h_{FE} classification in right table.

ITEM	E	F
h_{FE}	150~300	250~500
MARKING	M•E	M•F

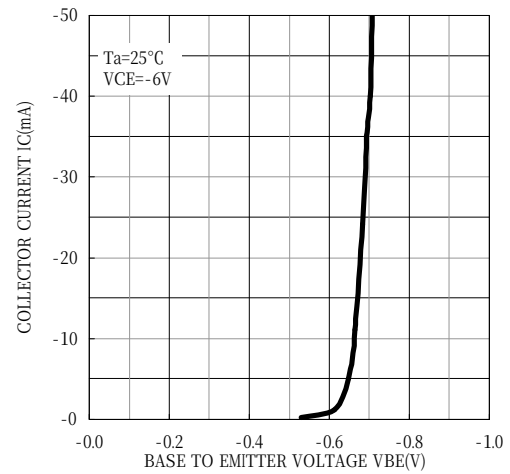
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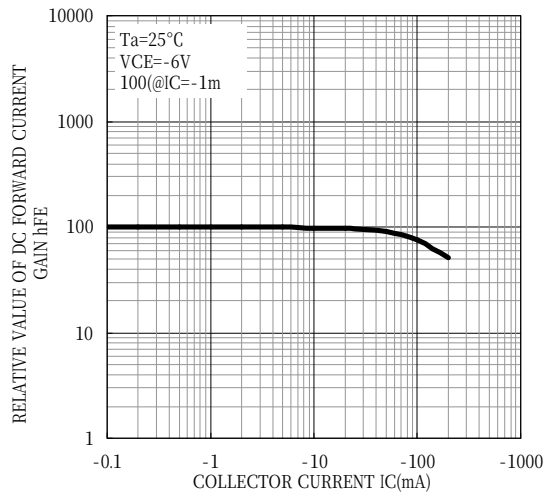
COMMON EMITTER OUTPUT



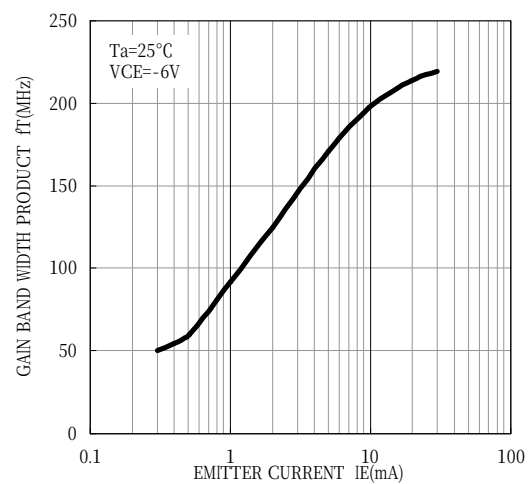
COMMON EMITTER TRANSFER



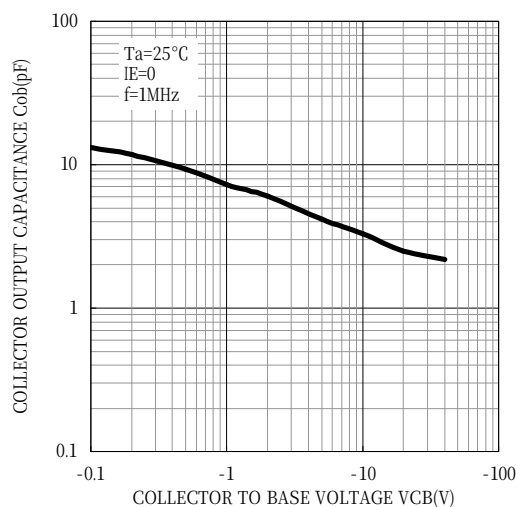
DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT



GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE
VS. COLLECTOR TO BASE VOLTAGE





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